



7NM65-FD2

Power MOSFET

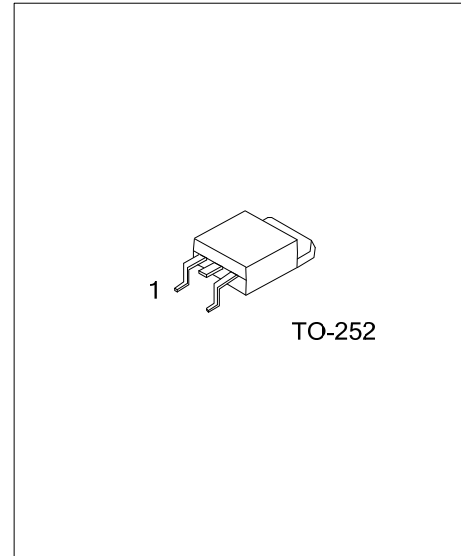
7A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

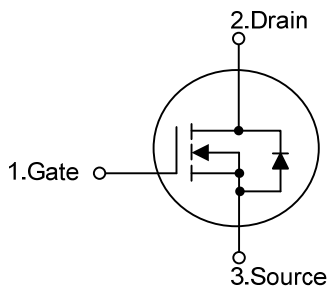
The **UTC 7NM65-FD2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} < 1.0 \Omega @ V_{GS}=10V, I_D=3.5A$
- * By using Super Junction Structure
- * Fast Switching
- * With 100% Avalanche Tested



SYMBOL



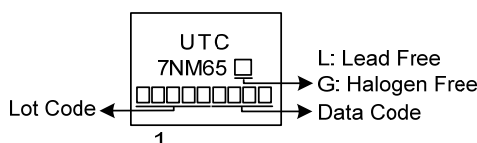
ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 7NM65L-TN3-R | 7NM65G-TN3-R | TO-252 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|---|
| <p>7NM65G-TN3-R</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p> | <p>(1) R: Tape Reel</p> <p>(2) TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p> |
|---|---|

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|------------------------|-----------|------------|------------------|
| Drain to Source Voltage | | V_{DSS} | 650 | V |
| Gate to Source Voltage | | V_{GSS} | ± 30 | V |
| Continuous Drain Current | Continuous | I_D | 7 | A |
| Pulsed Drain Current | Pulsed (Note 2) | I_{DM} | 21 | A |
| Avalanche Energy | Single Pulsed (Note 3) | E_{AS} | 162 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 8 | V/ns |
| Power Dissipation | | P_D | 60 | W |
| Junction Temperature | | T_J | +150 | $^\circ\text{C}$ |
| Storage Temperature | | T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=144\text{mH}$, $I_{AS}=1.5\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.

4. $I_{SD}\leq 10\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|---------------|---------|---------------------------|
| Junction to Ambient | θ_{JA} | 110 | $^\circ\text{C}/\text{W}$ |
| Junction to Case | θ_{JC} | 2.08 | $^\circ\text{C}/\text{W}$ |

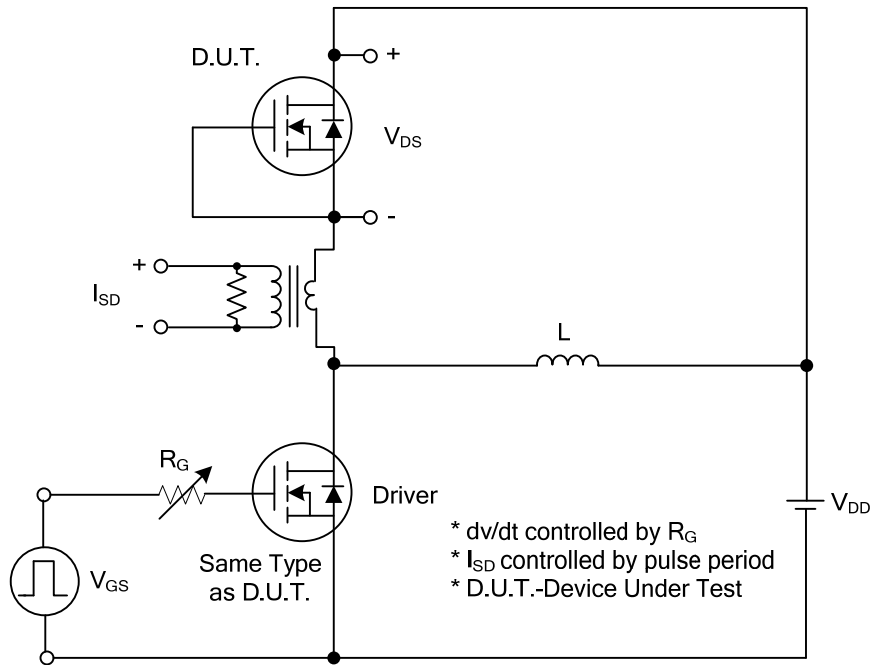
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--------------|--|-----|------|-----------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$ | 650 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$ | | | 10 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{DS}=0\text{V}$, $V_{GS}=\pm 30\text{V}$ | | | ± 100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$ | 2.5 | | 4.5 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=10\text{V}$, $I_D=3.5\text{A}$ | | | 1.0 | Ω |
| DYNAMIC PARAMETERS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$ | | 350 | | pF |
| Output Capacitance | C_{OSS} | | | 300 | | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 30 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Turn-ON Delay Time (Note 1) | $t_{D(ON)}$ | $V_{DD}=300\text{V}$, $V_{GS}=10\text{V}$, $I_D=7.0\text{A}$, $R_G=25\Omega$ (Note 1, 2) | | 0.4 | | ns |
| Rise Time | t_R | | | 10.2 | | ns |
| Turn-OFF Delay Time | $t_{D(OFF)}$ | | | 38 | | ns |
| Fall-Time | t_F | | | 20.2 | | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Maximum Body-Diode Continuous Current | I_S | | | | 7 | A |
| Maximum Body-Diode Pulsed Current | I_{SM} | | | | 21 | A |
| Drain-Source Diode Forward Voltage (Note 1) | V_{SD} | $I_S=7.0\text{A}$, $V_{GS}=0\text{V}$ | | | 1.4 | V |
| Body Diode Reverse Recovery Time (Note 1) | t_{rr} | $I_S=7.0\text{A}$, $V_{GS}=0\text{V}$ | | 166 | | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | $dI_F/dt=100\text{A}/\mu\text{s}$ | | 1 | | μC |

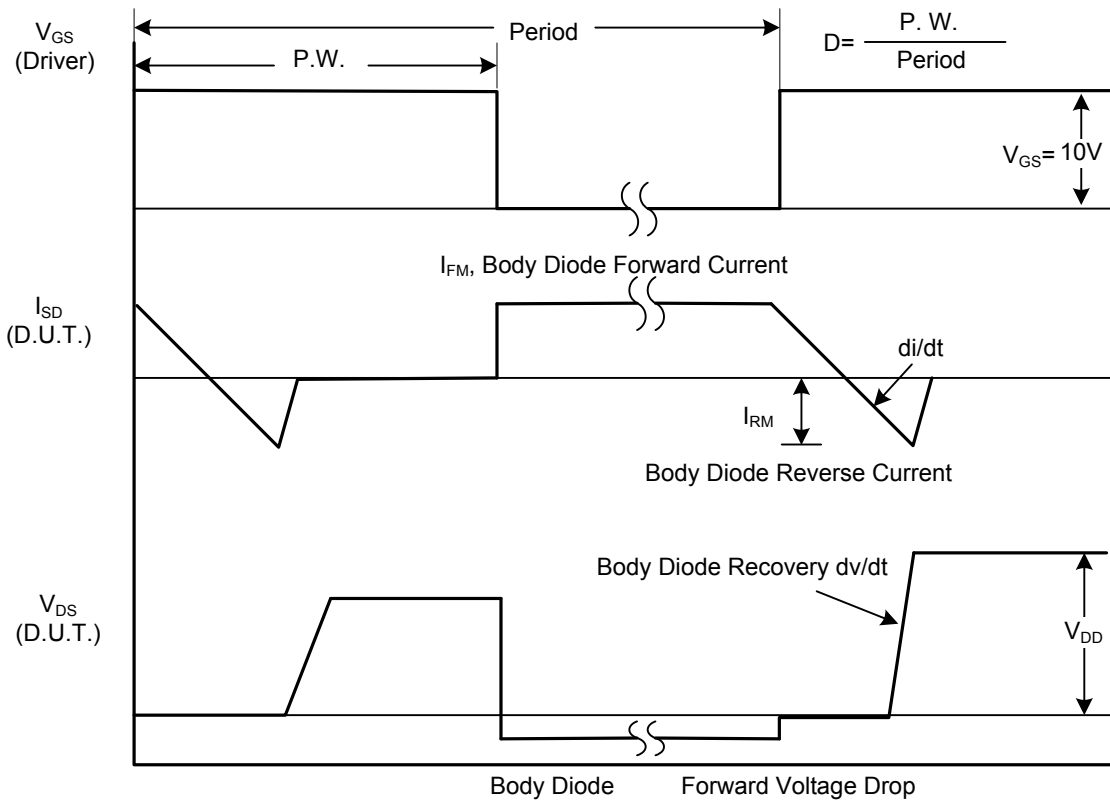
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

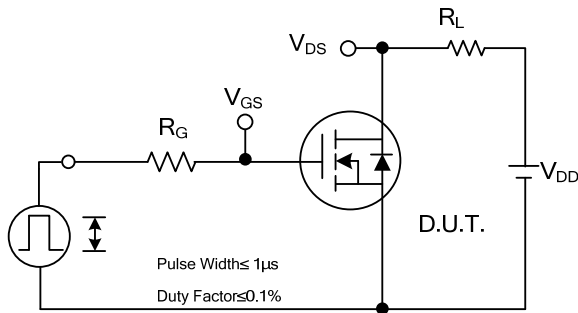


Peak Diode Recovery dv/dt Test Circuit

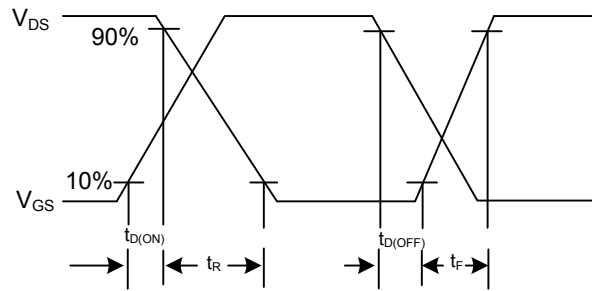


Peak Diode Recovery dv/dt Waveforms

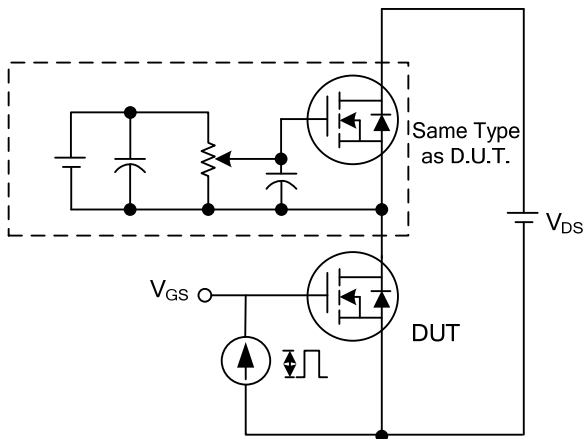
TEST CIRCUITS AND WAVEFORMS (Cont.)



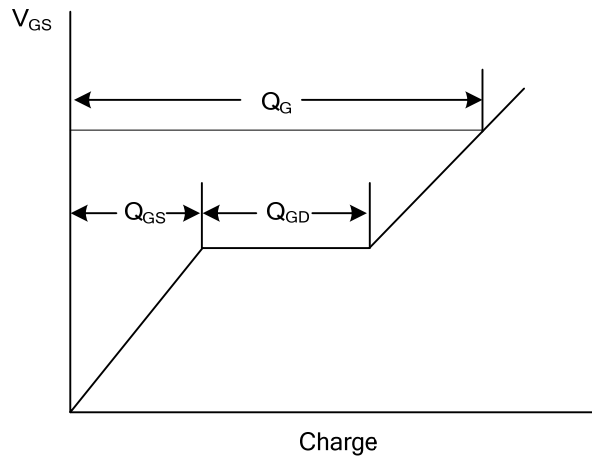
Switching Test Circuit



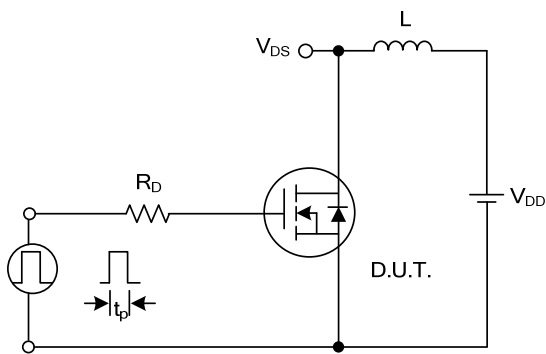
Switching Waveforms



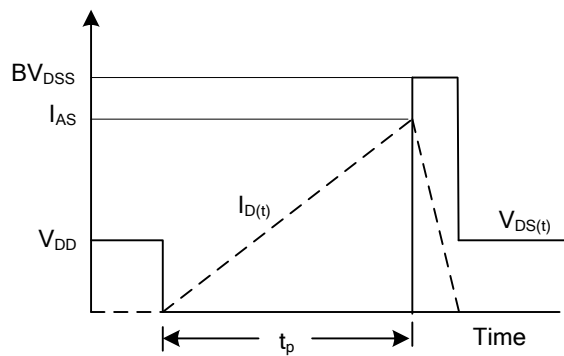
Gate Charge Test Circuit



Gate Charge Waveform

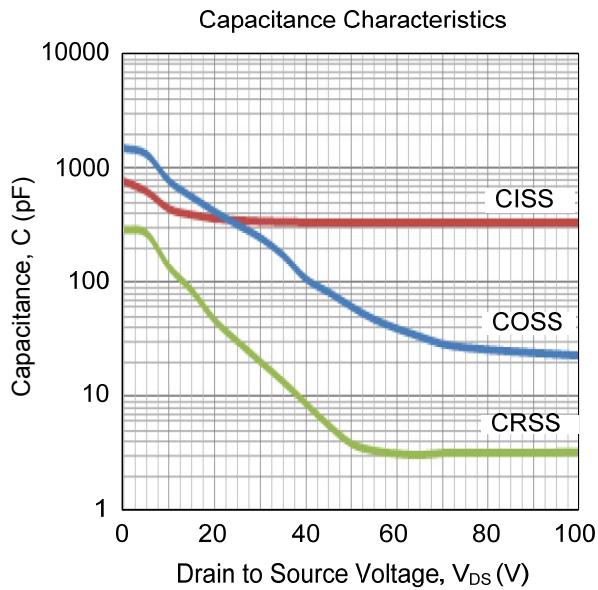


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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